

7. Memory and Programmable Logic

7.1 INTRODUCTION

Memory

RAM(random access memory): read and write operation

ROM(read only memory) : only read operation

Programmable Logic Device

PLD(programmable logic device)

PLA(programmable logic array)

(a) Conventional symbol

(b) Array logic symbol

PAL(programmable array logic)

Fig. 7-1 Conventional and Array Logic Diagrams for OR Gate

FPGA(field programmable gate array)



7.2 RANDOM-ACCESS MEMORY

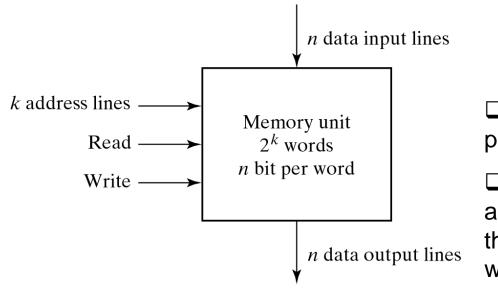


Fig. 7-2 Block Diagram of a Memory Unit

- ☐The address lines select one particular word.
- □A decoder inside the memory accepts this address and opens the paths needed to select the word specified.



7.2 RANDOM-ACCESS MEMORY

• 1024x16 Memory

Memory address

Binary	Decimal
0000000000	0
0000000001	1
0000000010	2
	:
1111111101	1021
1111111110	1022
1111111111	1023

Memory content

10110101010111101
1010101110001001
0000110101000110
:
:
1001110100010100
0000110100011110

The 1K * 16 memory has 10 bits in the address and 16 bits in each word.



7.2 RANDOM-ACCESS MEMORY - Write and Read Operations

- Write operation
- 1. Transfer the binary address of the desired word to the address lines.
- 2. Transfer the data bits that must be stored in memory to the data input lines.
- 3. Activate the write input
- Read operation
- 1. Transfer the binary address of the desired word to the address lines.
- 2. Activate the read input.

Table 7.1Control Inputs to Memory Chip

Memory Enable	Read/Write	Memory Operation	
0	X	None	
1	0	Write to selected word	
1	1	Read from selected word	



7.2 RANDOM-ACCESS MEMORY - Timing Waveforms

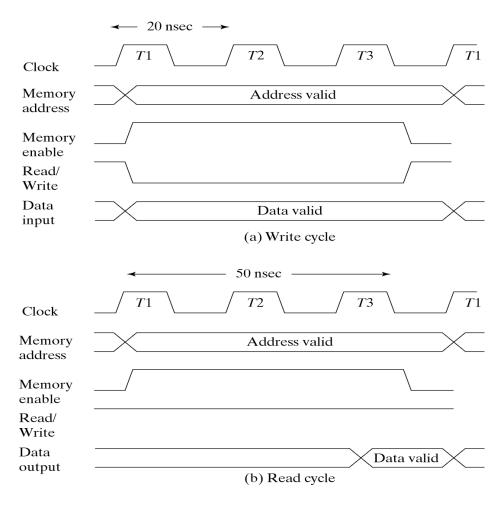


Fig. 7-4 Memory Cycle Timing Waveforms



7.2 RANDOM-ACCESS MEMORY - Types of Memories

□ Random access Memory -each word occupy one particular location.the access time is always the same ■ Sequential access Memory-information is read out only when the required word has been reached. the access time is variable. ■Volatile -Memory units lose the stored information when power is turned off. Nonvolatile-A nonvolatile memory retains its stored information after removal of power. ex) magnetic disk ,ROM(Read Only Memory) ■ Static RAM-The stored information remains valid as long as power is applied to the unit. Static **RAM** is easier to use and has shorter read and write cycles. □ Dynamic RAM-The capacitors must be periodically recharged by refreshing the dynamic memory. Dynamic **RAM** offers reduced power consumption and larger storage capacity



7.3 MEMORY DECODING - Internal Construction

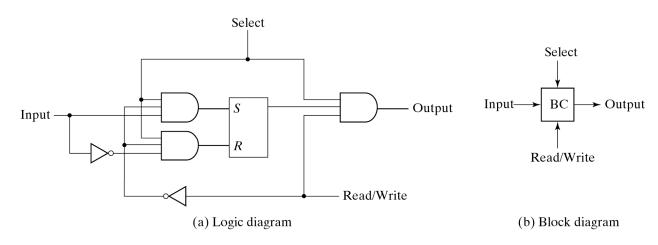


Fig. 7-5 Memory Cell

- ☐ The equivalent logic of a binary cell that stores one bit of information
- ☐ The binary cell stores one bit in its internal flip-flop
- □ It has three inputs and one output. The read/write input determines the cell operation when it is selected.



7.3 MEMORY DECODING - Internal Construction

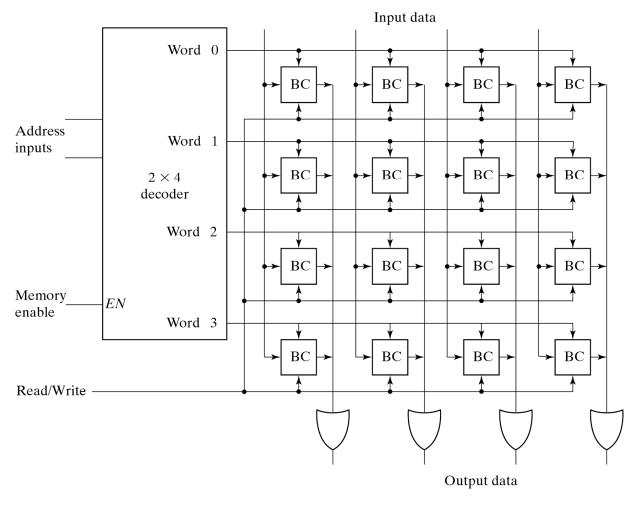


Fig. 7-6 Diagram of a 4×4 RAM

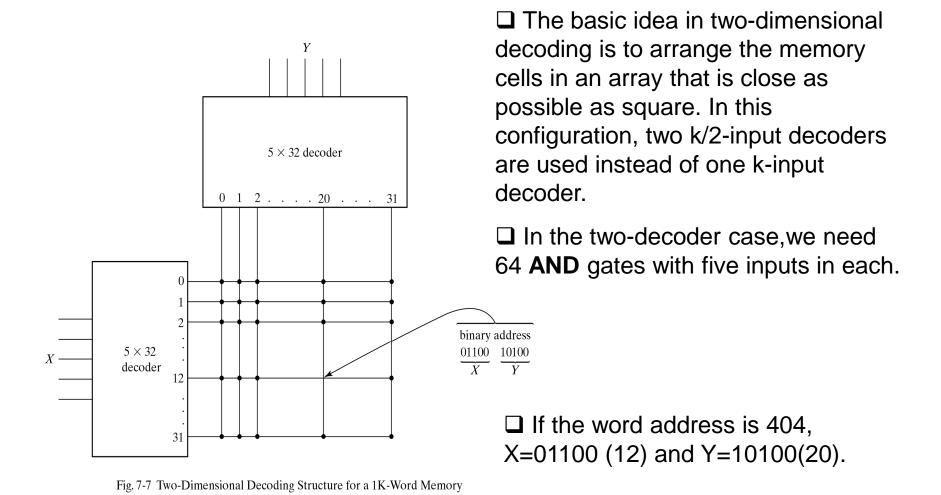


7.3 MEMORY DECODING - Internal Construction

☐ It has 16 binary cells
☐ Memory enable=0; all outputs of the decoder =0, none of the memory words are selected.
☐ Memory enable=1; one of the four words is selected. The read/write input determines the operation.
☐ During the read operation, the four bits of the selected word go through OR gates to the output terminals.
☐ During the write operation, the data available in the input lines are transferred into the four binary cells of the selected word.



7.3 MEMORY DECODING - Coincident Decoding





7.3 MEMORY DECODING - Address Multiplexing

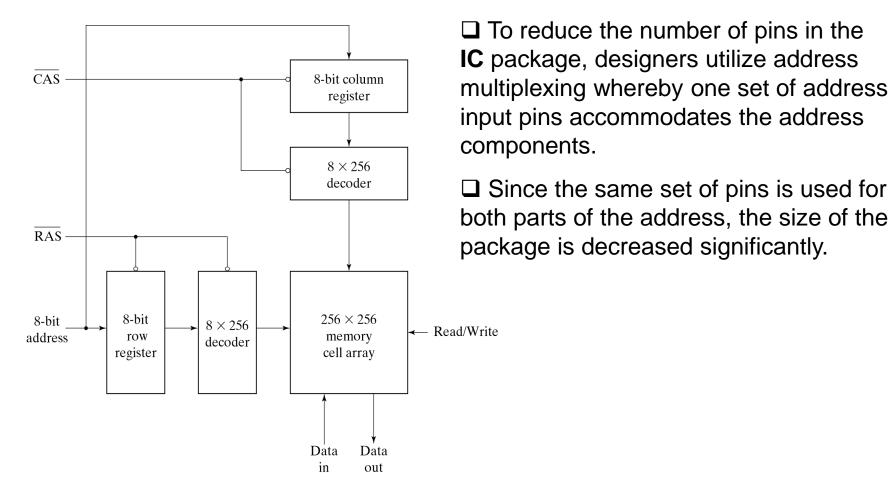


Fig. 7-8 Address Multiplexing for a 64K DRAM



7.4 ERROR DETECTION AND CORRECTION

8-bit data word =>11000100

Bit position 1 2 3 4 5 6 7 8 9 10 11 12

P₁ P₂ 1 P₄ 1 0 0 P₈ 0 1 0 0

 P_1 =**XOR** of bits(3,5,7,9,11)=0 (**XOR** performs the odd function.)

 $P_2=XOR$ of bits(3,6,7,10,11)=0

7-4

 P_4 =**XOR** of bits(5,6,7,12)=1

P₈=**XOR** of bits(9,10,11,12)=1

In memory, **Bit position** 1 2 3 4 5 6 7 8 9 10 11 12

0011100101 0 0

When the 12 bits are read from memory, The four check bits

 C_1 =**XOR** of bits (1,3,5,7,9,11) C_2 =**XOR** of bits (2,3,6,7,10,11)

 C_3 =**XOR** of bits (4,5,6,7,12) C_4 =**XOR** of bits (8,9,10,11,12)



7.4 ERROR DETECTION AND CORRECTION - Hamming code

Since the bits were stored with even parity $C=C_8C_4C_2C_1=0000$ (No error)

Bit position 1 2 3 4 5 6 7 8 9 10 11 12

001110010 1 0 0 No error

101110010 1 0 0 Error in bit 1

0011000101 0 0 Error in bit 5

Check bits C₈ C₄ C₂ C₁

With error in bit 1: 0 0 0 0

With error in bit 5: 0 1 0 1

The error can be corrected by complementing the corresponding bit.



7.4 ERROR DETECTION AND CORRECTION

- Single-Error Correction , Double-Error Detection

The **Hamming code** can detect and correct only a single error. Multiple errors are not detected.

To correct a single error and detect double errors, we **include the** additional parity bit.

If C=0 and P=0 No error occurred

If C=1 and p=1 A single error occurred, which can be corrected

If C=1 and P=0 A double error occurred, which is detected but cannot be corrected

If C=0 and P=1 An error occurred in the P₁₃ bit



7.5 READ-ONLY MEMORY

ROM=Decoder + **OR** gates

-permanent binary information is stored.

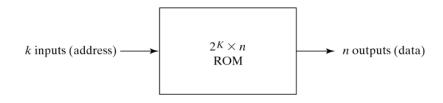


Fig. 7-9 ROM Block Diagram

k input lines and n output lines

The number of output lines ,n= the number of bits per word



7.5 READ-ONLY MEMORY

ROM = **AND** gates connected as a decoder + a number of **OR** gates 5 X 32 decoder has 32 **AND** gates and 5 inverters.

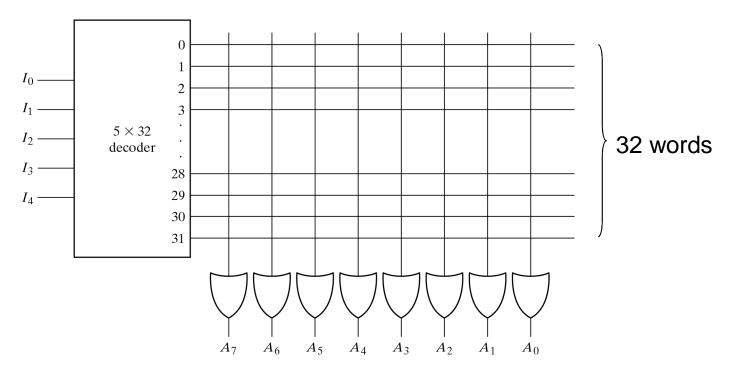


Fig. 7-10 Internal Logic of a 32×8 ROM



7.5 READ-ONLY MEMORY

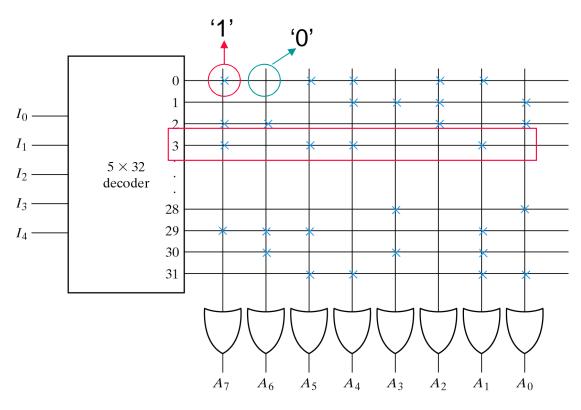
• ROM Truth Table(Partial)

Fable 7-3ROM Truth Table (Partial)

	In	npu	ts					Out	puts			
14	13	12	11	10	A7	A6	A5	A4	А3	A2	A1	AO
0	0	0	0	0	1	0	1	1	0	1	1	0
0	0	0	0	1	0	0	0	1	1	1	0	1
0	0	0	1	0	1	1	0	0	0	1	0	1
0	0	0	1	1	1	0	1	1	0	0	1	0
		:					:					
1	1	1	0	0	0	0	0	0	1	0	0	1
1	1	1	0	1	1	1	1	0	0	0	1	0
1	1	1	1	0	0	1	0	0	1	0	1	0
1	1	1	1	1	0	0	1	1	0	0	1	1



7.5 READ-ONLY MEMORY - Combinational Circuit Implementation



 $A_7(I_4,I_3,I_2,I_0)$ =Sum of minterms(0,2,3,...,29)

Input->00011(3)

Others-> all '0'

Output->10110010





7.5 READ-ONLY MEMORY - Combinational Circuit Implementation

• EXAMPLE 7-1

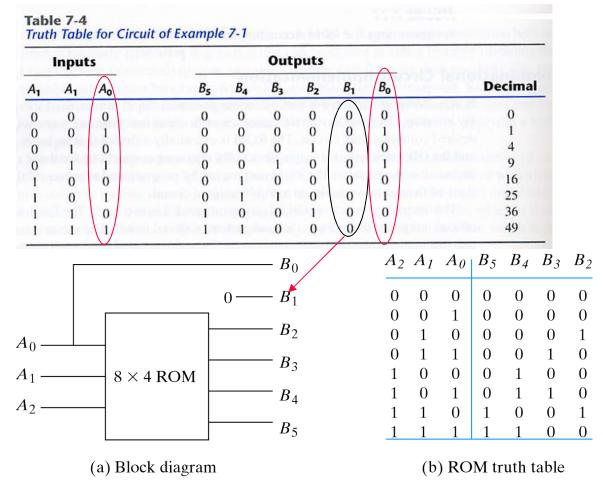


Fig. 7-12 ROM Implementation of Example 7-1



7.5 READ-ONLY MEMORY - Types of ROMs

For large quantities, mask programming is economical.

For small quantities, programmable read-only memory(**PROM**) is more economical.(all '1's)

PROM- irreversible and permanent

EPROM(Erasable PROM)- can be restructured to the initial value(**UV** light->discharge)

EEPROM(Electrically erasable PROM)- can be erased with electrical signals instead ultra violet light.



7.5 READ-ONLY MEMORY - Combinational PLDs

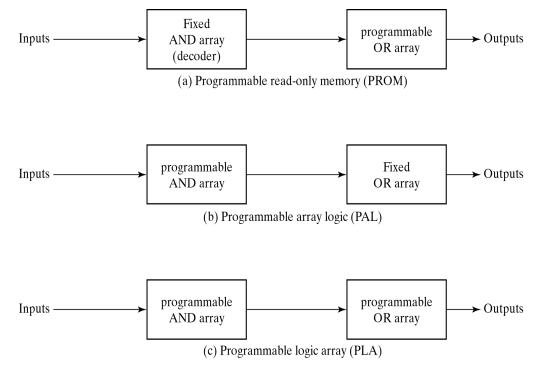
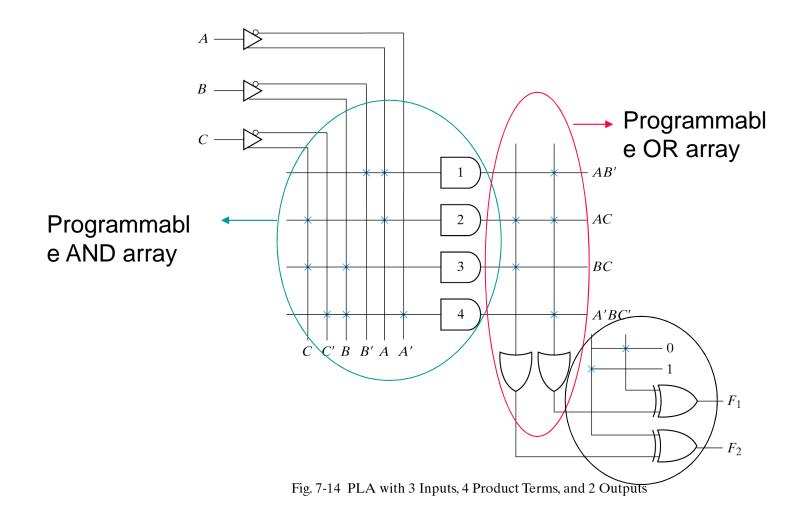


Fig. 7-13 Basic Configuration of Three PLDs

- □A combinational PLD is an IC with programmable gates divided into an AND array and an OR array to provide an AND-OR sum of product implementation.
- ☐Three major types PLDs
- (a)fixed AND array +programmable OR array
- **(b)**programmable **AND** array + fixed **OR** array
- (c)programmable AND array + programmable OR array



7.6 PROGRAMMABLE LOGIC ARRAY





7.6 PROGRAMMABLE LOGIC ARRAY

PLA Programming Table

- □The PLA does not provide full decoding of the variables.(decoder <->AND array)
- □The PLA consists of **n** inputs ,**m** outputs , **k** product terms(AND gate) ,and **m** sum terms(OR gate)
- □ The number of programmed fuses is 2n*k+k*m+m
- , whereas that of a **ROM** is $2^n * m$

$$\Box$$
F₁=AB' + AC + A'BC'
F₂= (AC + BC)'

Table 7-5 *PLA Programming Table*

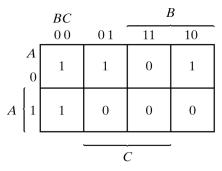
					Out	hars
			Input	s	(T)	(C)
	Product Term	A	В	c	F ₁	F ₂
AB'	1	1	0	-	1	_
AC	2	1	-	1	1	1
BC	3		1	1	-5	1
A'BC'	4	0	1	0	1	_



Outnute

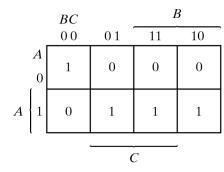
7.6 PROGRAMMABLE LOGIC ARRAY

• EXAMPLE 7-2



$$F_1 = A'B' + A'C' + B'C'$$

 $F_1 = (AB + AC + BC)'$



$$F_2 = AB + AC + A'B'C'$$

$$F_2 = (A'C + A'B + AB'C')'$$

$$F_{1}(A, B, C) = \sum (0,1,2,4)$$

$$F_{2}(A, B, C) = \sum (0,5,6,7)$$

$$F_{1} = (AB + AC + BC)'$$

$$F_{2} = AB + AC + A'B'C'$$

PLA programming table

		1 0	\mathcal{C}	
			Out	puts
	Product	Inputs	(C)	(T)
	term	A B C	F_1	F_2
AB	1	1 1 –	1	1
AC	2	1 - 1	1	1
BC	3	- 1 1	1	_
A'B'C'	4	0 0 0	_	1

Fig. 7-15 Solution to Example 7-2



7.7 PROGRAMMABLE ARRAY LOGIC

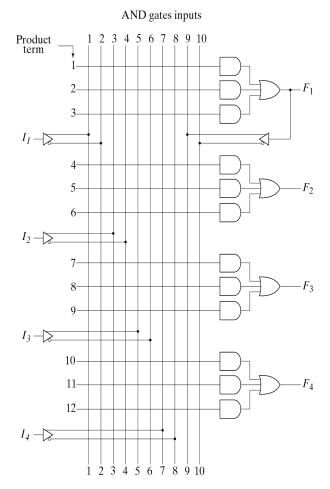


Fig. 7-16 PAL with Four Inputs, Four Outputs, and Three-Wide AND-OR Structure

PAL-With a fixed **OR** array and a programmable **AND** array.

-Not as flexible as the **PLA**(Only the **AND** gate are programmable.)



7.7 PROGRAMMABLE ARRAY LOGIC

Table 7-6

10

PAL Programming Table

Example(PAL)

$$w(A,B,C,D) = \sum (2,12,13)$$

$$x(A,B,C,D) = \sum (7,8,9,10,11,12,12,14,15)$$

$$y(A,B,C,D) = \sum (0,2,3,4,5,6,7,8,10,11,15)$$

$$z(A,B,C,D) = \sum (1,2,8,12,13,)$$

$$w = ABC' + A'B'CD'$$

$$x = A + BCD$$

$$y = A'B + CD + B'D'$$

$$z = ABC' + A'B'CD' + AC'D' + A'B'C'D$$

$$= w + AC'D' + A'B'C'D$$

		AN	ID In			
Product Term	A	В	С	D	W	Outputs
1	1	1	0	-	_	w = ABC'
2	0	0	1	0	-	+ A'B'CD'
3			-	-	-	
4	1	-	-		-	x = A
5	-	1	1	1	-	+ BCD
6	-	-	-	-	-	
7	0	1	_	_	_	y = A'B
8	_	_	1	1	_	+ CD
9	_	0	_	0	-	+ B'D'



+ AC'D'

+ A'B'C'D

7.7 PROGRAMMABLE ARRAY LOGIC

•Fuse Map for PAL

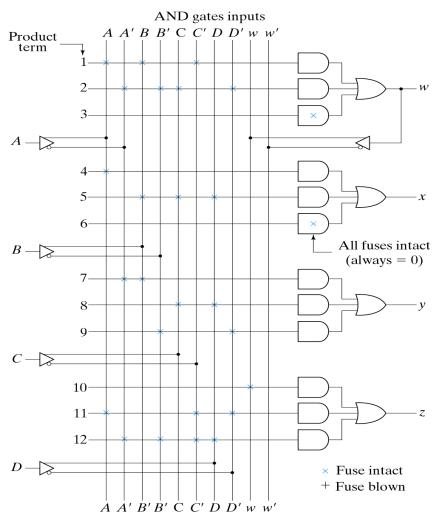


Fig. 7-17 Fuse Map for PAL as Specified in Table 7-6



- 1. Sequential(or simple) Programmable Logic Device (SPLD)
- 2. Complex Programmable Logic Device(CPLD)
- 3. Field Programmable Gate Array(**FPGA**)

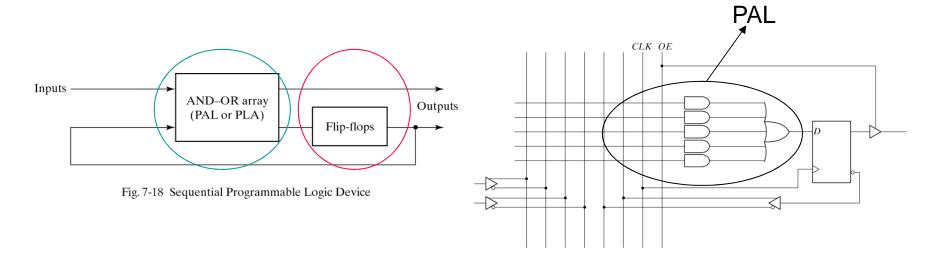


Fig. 7-19 Basic Macrocell Logic



CPLD &FPGA

CPLD-a collection of individual PLDs

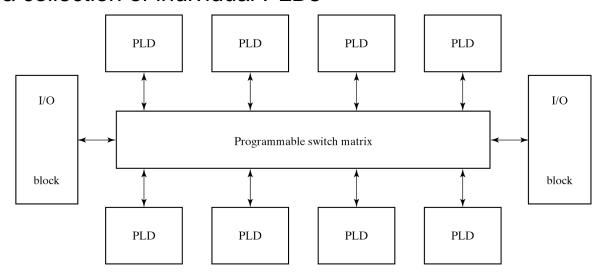
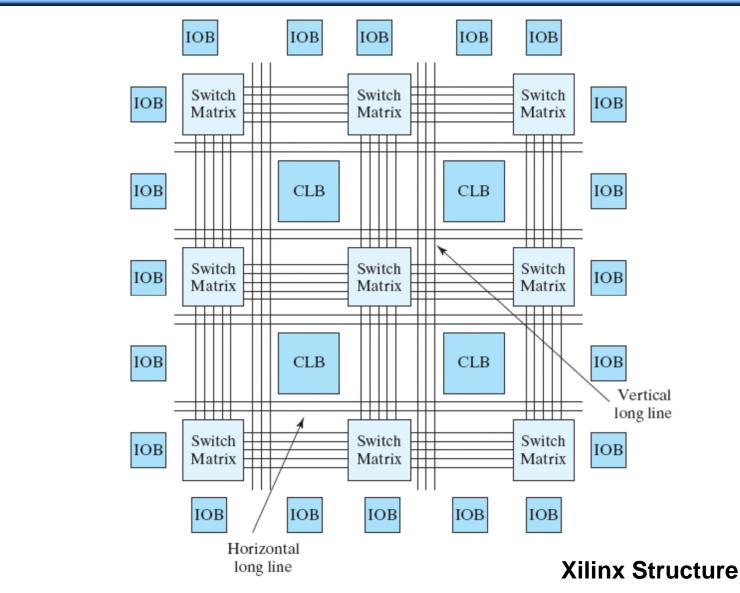


Fig. 7-20 General CPLD Configuration

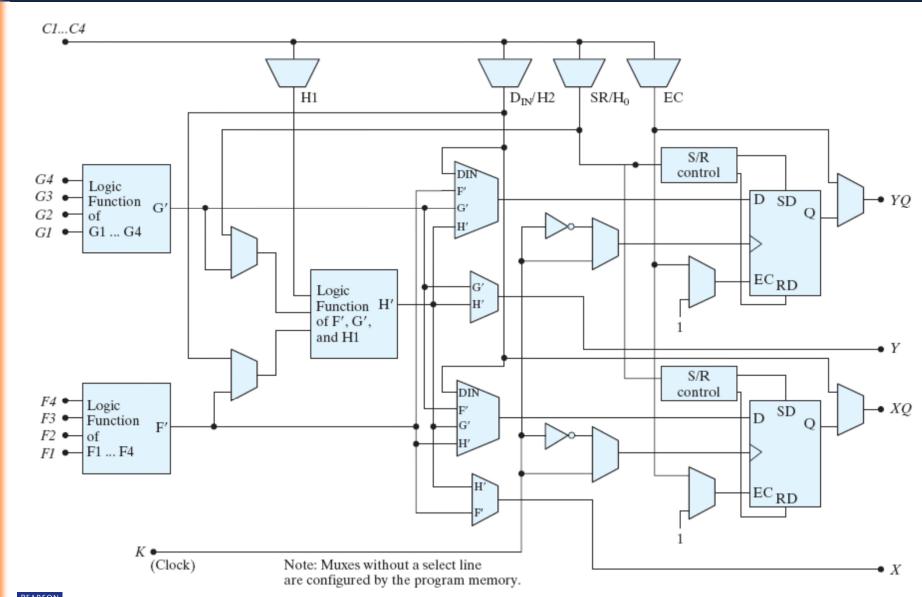
FPGA(Field Programmable Gate Array)

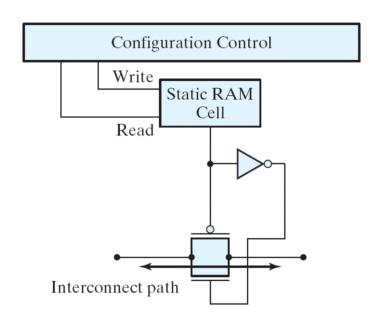
- -a **VLSI** circuit that can be programmed in the user's location.
- -look-up tables, multiplexes, gates, and flip-flops

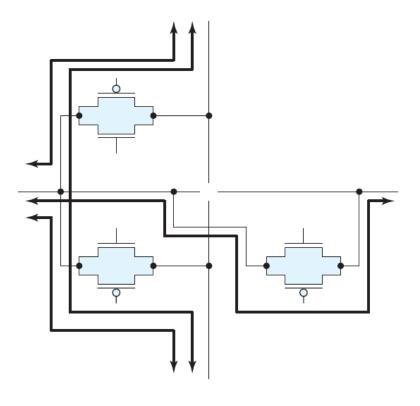




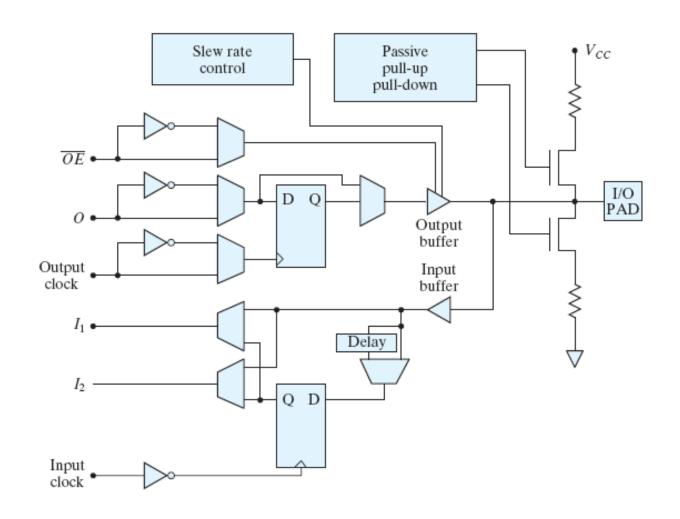




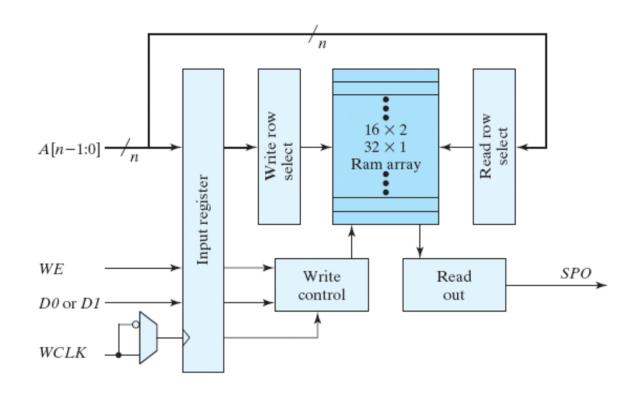














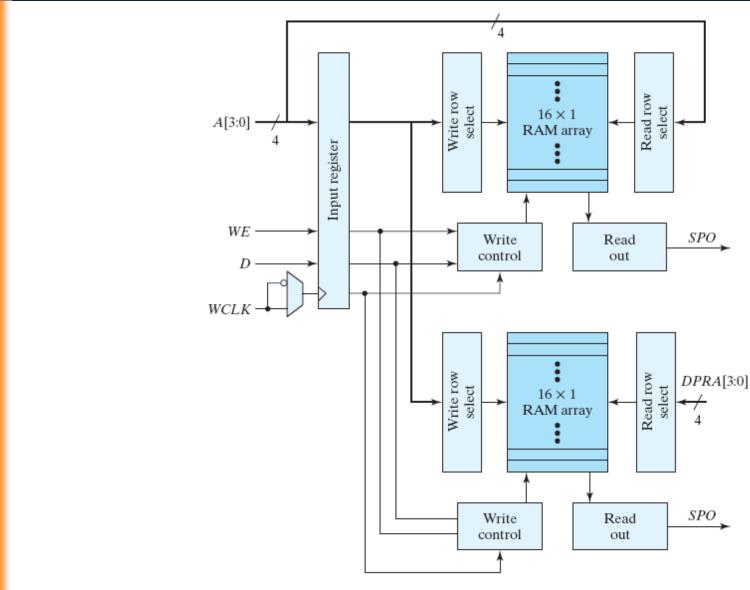




Table 7.7Attributes of the Xilinx Spartan XL Device Family

Spartan XL	XCS05/XL	XCS10/XL	XCS20/XL	XCS30/XL	XCS40/XL
System Gates ¹	2K-5K	3K-10K	7K-20K	10K-30K	13K-40K
Logic Cells ²	238	466	950	1,368	1,862
Max Logic Gates	3,000	5,000	10,000	13,000	20,000
Flip-Flops	360	616	1,120	1,536	2,016
Max RAM Bits	3,200	6,272	12,800	18,432	25,088
Max Avail I/O	77	112	160	192	224

^{1 20-30%} of CLBs as RAM.

Table 7.8 *Spartan II Device Attributes*

Spartan II FPGAs	XC2S15	XC2S30	XC2550	XC2S100	XC2S150	XC2S200
System Gates ¹	6K-15K	13K-30K	23K-50K	37K-100K	52K-150K	71K-200K
Logic Cells ²	432	972	1,728	2,700	3,888	5,292
Block RAM Bits	16,384	24,576	32,768	40,960	49,152	57,344
Max Avail I/O	86	132	176	196	260	284

¹ 20-30% of CLBs as RAM.

² 1 Logic cell = four-input lookup table + flip-flop.



² 1 Logic cell = four-input lookup table + flip-flop.

Table 7.9 *Comparison of the Spartan Device Families*

Part	Spartan	Spartan XL	Spartan II	
Architecture	XC4000 Based	XC4000 Based	Virtex Based	
Max # System Gates	5K-40K	5K-40K	15K-200K	
Memory	Distributed RAM	Distributed RAM	Block + Distributed	
I/O Performance	80 MHz	100 MHz	200 MHz	
I/O Standards	4	4	16	
Core Voltage	5 V	3.3 V	2.5 V	
DLLs	No	No	Yes	



